

Notice of References Cited	Application/Control No. 09/836,449	Applicant(s)/Patent Under Reexamination FONASH ET AL.	
	Examiner Richard A. Booth	Art Unit 2812	Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	B	US-5,242,863	09-1993	Xiang-Zheng et al.	438/53
	C	US-5,352,635	10-1994	Tu et al.	438/53
	D	US-6,248,422	06-2001	Robbie et al.	428/119
	E	US-5,262,000	11-1993	Welbourn et al.	216/2
	F	US-6,048,734	04-2000	Burns et al.	436/180
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	K	US-			
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	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kalkan et al., "Nanocrystalline Si Thin Films with arrayed void-column network deposited by high density plasma", Journal of Applied Physics, Volume 88, Number 1, July 2000, pages 555-561.
	V	Tayanaka et al., "Thin-Film Crystalline Silicon Solar Cells Obtained by Separation of a Porous Silicon Sacrificial Layer", 2 nd World Conference and Exhibition on Photovoltaic Solar Energy Conversion, July 6, 1998, pages 1272-1277.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.